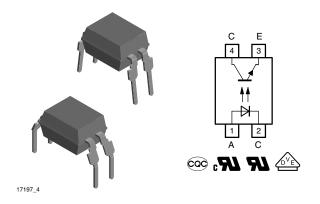
Vishay Semiconductors

Optocoupler, Phototransistor Output, High Temperature



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LINKS TO ADDITIONAL RESOURCES



DESCRIPTION

The TCET110. consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 4-lead plastic dual inline package.

AGENCY APPROVALS

- UL 1577
- <u>cUL 1577</u>
- DIN EN 60747-5-5 (VDE 0884-5)
- BSI: EN 62368-1:2014
- CQC GB4943.1-2011
- CQC GB8898-2011

FEATURES

- High common mode rejection
- Low temperature coefficient of CTR
- CTR offered in 7 groups
- Reinforced isolation provides circuit protection against electrical shock (safety class II)
- Isolation materials according to UL 94 V-0
- Pollution degree 2 (DIN / VDE 0110 / resp. IEC 60664)
- Climatic classification 55 / 100 / 21 (IEC 60068 part 1)
- Rated impulse voltage (transient overvoltage) $V_{IOTM} = 6 kV_{peak}$
- Isolation test voltage (partial discharge test voltage) $V_{pd} = 1.6 \text{ kV}$
- Rated isolation voltage (RMS includes DC) $V_{IOWM} = 600 V_{RMS}$
- Rated recurring peak voltage (repetitive) V_{IORM} = 848 V_{peak}
- Creepage current resistance according to VDE 0303 / IEC 60112 comparative tracking index: CTI ≥ 175
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):

- For application class I to IV at mains voltage ≤ 300 V
- For application class I to III at mains voltage ≤ 600 V according to DIN EN 60747-5-5 (VDE 0884), suitable for:
 - Switch-mode power supplies
 - Line receiver
 - Computer peripheral interface
 - Microprocessor system interface

ORDERING INFORMATION									
Т	С	E T	1	1 0	#	#			Ŋ
		PARTI	NUMBER			LEAD FORM		7.62 mm	+ I
AGENCY	CTR (%)								
CERTIFIED / PACKAGE					10 mA				
UL, cUL, VDE, BSI, CQC	50 to 600	40 to 80	63 to 125	100 to 200	160 to 320	100 to 300	80 to 160	130 to 260	200 to 400
DIP-4	TCET1100	-	TCET1102	TCET1103	-	TCET1106	TCET1107	TCET1108	TCET1109
DIP-4, 400 mil	TCET1100G	TCET1101G	TCET1102G	TCET1103G	TCET1104G	TCET1106G	TCET1107G	TCET1108G	TCET1109G

Note

G = lead form 10.16 mm; G is not marked on the body

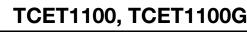
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RoHS

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ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25 \degree C$, unless otherwise specified)									
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT					
INPUT									
Reverse voltage		V _R	6	V					
Forward current		١ _F	60	mA					
Forward surge current	$t_p \le 10 \ \mu s$	I _{FSM}	1.5	A					
OUTPUT									
Collector emitter voltage		V _{CEO}	70	V					
Emitter collector voltage		V _{ECO}	7	V					
Collector current		I _C	50	mA					
Collector peak current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I _{CM}	100	mA					
COUPLER									
Isolation test voltage (RMS)	t = 1 min	V _{ISO}	5000	V _{RMS}					
Operating ambient temperature range		T _{amb}	-40 to +100	°C					
Storage temperature range		T _{stg}	-55 to +125	°C					
Soldering temperature ⁽¹⁾	2 mm from case, \leq 10 s	T _{sld}	260	О°					

Notes

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not
implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute
maximum ratings for extended periods of the time can adversely affect reliability

⁽¹⁾ Refer to wave profile for soldering conditions for through hole devices

THERMAL CHARACTERISTICS			
PARAMETER	SYMBOL	VALUE	UNIT
LED power dissipation	P _{diss}	100	mW
Output power dissipation	P _{diss}	150	mW
Maximum LED junction temperature	T _{jmax.}	125	°C
Maximum output die junction temperature	T _{jmax.}	125	°C
Thermal resistance, junction emitter to board	θ_{EB}	173	°C/W
Thermal resistance, junction emitter to case	θ_{EC}	149	°C/W
Thermal resistance, junction detector to board	θ_{DB}	111	°C/W
Thermal resistance, junction detector to case	θ_{DC}	127	°C/W
Thermal resistance, junction emitter to junction detector	θ_{ED}	173	°C/W
Thermal resistance, board to ambient (1)	θ_{BA}	197	°C/W
Thermal resistance, case to ambient (1)	θ_{CA}	4041	°C/W

Notes

• The thermal model is represented in the thermal network below. Each resistance value given in this model can be used to calculate the temperatures at each node for a given operating condition. The thermal resistance from board to ambient will be dependent on the type of PCB, layout and thickness of copper traces. For a detailed explanation of the thermal model, please reference Vishay's "Thermal Characteristics of Optocouplers" application note

⁽¹⁾ For 2 layer FR4 board (4" x 3" x 0.062")

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ELECTRICAL CHARACTERISTICS ($T_{amb} = 25 \text{ °C}$, unless otherwise specified)									
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT			
INPUT									
Forward voltage	I _F = 50 mA	V _F	-	1.25	1.6	V			
Junction capacitance	$V_R = 0$, f = 1 MHz	Cj	-	50	-	pF			
OUTPUT									
Collector emitter voltage	I _C = 1 mA	V _{CEO}	70	-	-	V			
Emitter collector voltage	I _E = 100 μA	V _{ECO}	7	-	-	V			
Collector emitter cut-off current	$V_{CE} = 20 V, I_F = 0 A, E = 0$	I _{CEO}	-	10	100	nA			
COUPLER									
Collector emitter saturation voltage	I _F = 10 mA, I _C = 1 mA	V _{CEsat}	-	-	0.3	V			
Cut-off frequency	V_{CE} = 5 V, I_F = 10 mA, R_L = 100 Ω	f _c	-	110	-	kHz			
Coupling capacitance	f = 1 MHz	C _k	-	0.3	-	pF			

Note

• Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements

CURRENT TRANSFER RATIO									
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT		
		TCET1101G	CTR	13	30	-	%		
	(1 - 5)(1 - 1)	TCET1102, TCET1102G	CTR	22	45	-	%		
	V _{CE} = 5 V, I _F = 1 mA	TCET1103, TCET1103G	CTR	34	70	-	%		
		TCET1104G	CTR	56	90	-	%		
		TCET1100, TCET1100G	CTR	50	-	600	%		
I _C /I _F		TCET1106, TCET1106G	CTR	100	-	300	%		
	$V_{CE} = 5 \text{ V}, I_F = 5 \text{ mA}$	TCET1107, TCET1107G	CTR	80	-	160	%		
'U' 'F		TCET1108, TCET1108G	CTR	130	-	260	%		
		TCET1109, TCET1109G	CTR	200	-	400	%		
		TCET1101, TCET1101G	CTR	40	-	80	%		
	V 5V 10 mA	TCET1102, TCET1102G	CTR	63	-	125	%		
	$V_{CE} = 5 \text{ V}, \text{ I}_{F} = 10 \text{ mA}$	TCET1103, TCET1103G	CTR	100	-	200	%		
		TCET1104, TCET1104G	CTR	160	-	320	%		



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MAXIMUM SAFETY RATINGS									
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT			
INPUT									
Forward current		IF	-	-	130	mA			
OUTPUT									
Power dissipation		P _{diss}	-	-	265	mW			
COUPLER									
Rated impulse voltage		V _{IOTM}	-	-	6	kV			
Safety temperature		T _{si}	-	-	150	°C			

Note

According to DIN EN 60747-5-5 (see figure 2). This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits

INSULATION RATED PARAMETERS									
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Partial discharge test voltage - routine test	100 %, t _{test} = 1 s	V _{pd}	1.6	-	-	kV			
Partial discharge test voltage - lot test (sample test)	$t_{Tr} = 60 \text{ s}, t_{test} = 10 \text{ s},$ (see figure 2)	V _{IOTM}	6	-	-	kV			
		V _{pd}	1.3	-	-	kV			
	V _{IO} = 500 V	R _{IO}	10 ¹²	-	-	Ω			
Insulation resistance	$V_{IO} = 500 \text{ V}, \text{ T}_{amb} = 100 ^{\circ}\text{C}$	R _{IO}	10 ¹¹	-	-	Ω			
	V _{IO} = 500 V, T _{amb} = 150 °C (construction test only)	R _{IO}	10 ⁹	-	-	Ω			

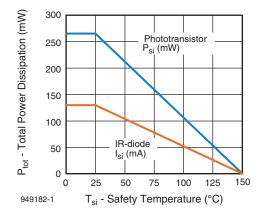


Fig. 1 - Derating Diagram

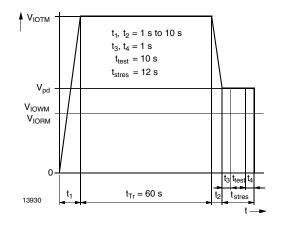


Fig. 2 - Test Pulse Diagram for Sample Test According to DIN EN 60747-5-5 / DIN EN 60747-; IEC 60747

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For technical questions, contact: optocoupleranswers@vishay.com

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SWITCHING CHARACTERISTICS

Rise time	V_S = 5 V, I _C = 2 mA, R _L = 100 Ω , (see Fig. 3)	t _r	-	3	I
Turn-on time	V_{S} = 5 V, I _C = 2 mA, R _L = 100 Ω , (see Fig. 3)	t _{on}	-	6	-
Storage time	V_S = 5 V, I _C = 2 mA, R _L = 100 Ω , (see Fig. 3)	ts	-	0.3	-
Fall time	V_S = 5 V, I _C = 2 mA, R _L = 100 Ω , (see Fig. 3)	t _f	-	4.7	-
Turn-off time	V_S = 5 V, I _C = 2 mA, R _L = 100 Ω , (see Fig. 3)	t _{off}	-	5	-
Turn-on time	$\label{eq:VS} \begin{split} V_S = 5 \text{ V}, \text{ I}_F = 10 \text{ mA}, \text{ R}_L = 1 \text{ k}\Omega, \\ (\text{see Fig. 4}) \end{split}$	t _{on}	-	9	-
Turn-off time	V_S = 5 V, I _F = 10 mA, R _L = 1 k Ω , (see Fig. 4)	t _{off}	-	10	-

SYMBOL

t_d

TEST CONDITION

 $V_S = 5 V$, $I_C = 2 mA$, $R_L = 100 \Omega$,

(see Fig. 3)

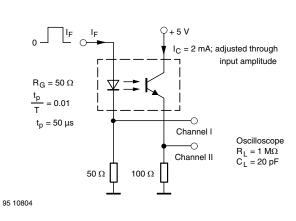


Fig. 3 - Test Circuit, Non-Saturated Operation

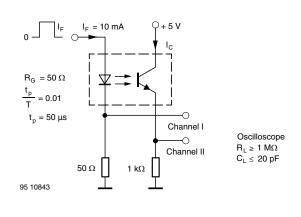
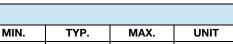


Fig. 4 - Test Circuit, Saturated Operation



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μs

μs

μs

μs

μs

μs

μs

μs

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TCET1100, TCET1100G

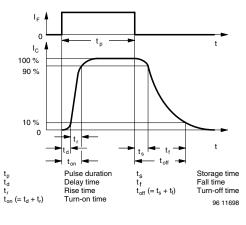
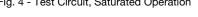


Fig. 5 - Switching Times





PARAMETER

Delay time





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TYPICAL CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

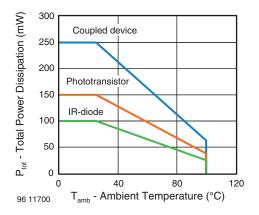


Fig. 6 - Total Power Dissipation vs. Ambient Temperature

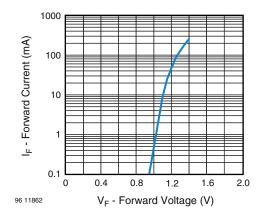
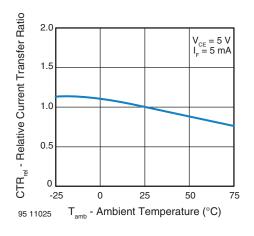


Fig. 7 - Forward Current vs. Forward Voltage





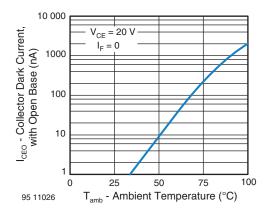


Fig. 9 - Collector Dark Current vs. Ambient Temperature

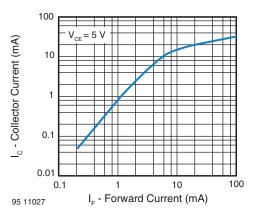


Fig. 10 - Collector Current vs. Forward Current

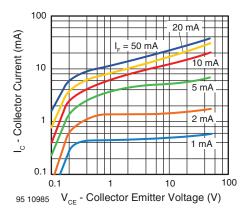


Fig. 11 - Collector Current vs. Collector Emitter Voltage

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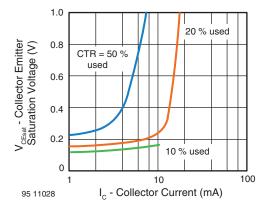


Fig. 12 - Collector Emitter Saturation Voltage vs. **Collector Current**

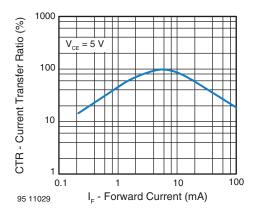
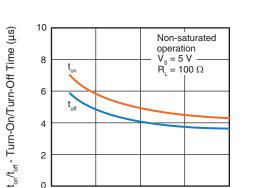


Fig. 13 - Current Transfer Ratio vs. Forward Current



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0 2 4 6 I_c - Collector Current (mA) 95 11030

0

Fig. 14 - Turn-On / Off Time vs. Collector Current

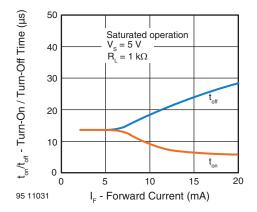


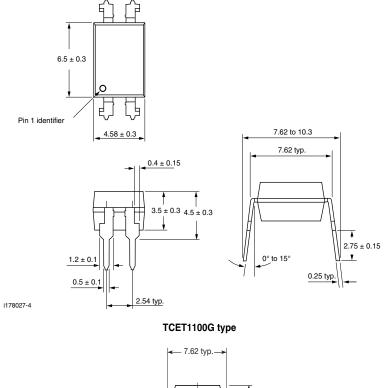
Fig. 15 - Turn-On / Off Time vs. Forward Current

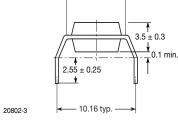
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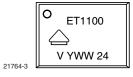
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PACKAGE DIMENSIONS in millimeters





PACKAGE MARKING





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